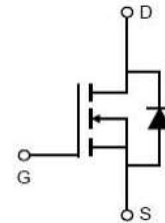




1. Description

SS086N68TT, the N-channel Enhanced Power MOSFETs, is obtained by advanced trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

Schematic Diagram



KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	68	V
I_D	80	A
$R_{DS(on).typ}$	7	mΩ

FEATURES:

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 8.6m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS:

- Switching applications
- Motor drivers
- Synchronous rectification

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS086N68TT	TO-220	SS086N68TT	Tube

